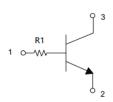
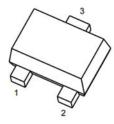




NPN Digital Transistors (Built-in Resistors)





1. IN

2. GND

SOT-723 3. OUT

Features

- Moisture sensitivity level 1
- Halogen free and RoHS compliant
- Surface mount package ideally suited for auto matic insertion

Application

- Signal amplification
- Switching circuit

Mechanical data

• Package: SOT-723

• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

■ Maximum Ratings (Ta=25°C Unless otherwise specified)

ltem	Symbol	Unit	Conditions	Value
Device marking code				03
Collector-base voltage	V _{CBO}	V	I _C =50uA,I _E =0	50
Collector-emitter voltage	V _{CEO}	V	I _C =1mA,I _B =0	50
Emitter-base voltage	V _{EBO}	V	I _E =50uA,I _C =0	5
Collector current	Ic	mA		100
Power dissipation	P _D	mW		100
Junction temperature	TJ	°C		-55 to +150
Storage temperature	T _{STG}	°C		-55 to +150



DTC143TM



■ Electrical Characteristics (T_a=25°C Unless otherwise specified)

Item	Symbol	Unit	Conditions	Min	Тур	Max
Collector-base breakdown voltage	llector-base breakdown voltage $V_{(BR)CBO}$ V $I_C=50uA,I_E=0$		I _C =50uA,I _E =0	50		
Collector-emitter breakdown voltage	V _{(BR)CEO}	V	I _C =1mA,I _B =0	50		
Emitter-base breakdown voltage	V _{(BR)EBO}	V	I _E =50uA,I _C =0	5		
Collector-base cutoff current	І _{сво}	uA	V _{CB} =50V,I _E =0			0.5
Collector-emitter cutoff current	I _{EBO}	uA	V _{EB} =4V, I _C =0V			0.5
	h _{FE}		V _{CE} =5V, I _C =1mA	100		600
Collector-emitter saturation voltage	V _{CE(sat)}	V	I _C =5mA,I _B =0.25mA			0.3
Input resistance	R ₁	kΩ		3.29	4.7	6.11
Transition frequency	f _T	MHz	V _{CE} =10V,I _C =5mA,f=100MHz		250	

■ Thermal Characteristics

Parameter	Symbol	Unit	Value
Thermal resistance, junction-to-ambient	RθJ-A ⁽¹⁾	°C/W	1250
Thermal resistance, junction-to-case	R ₀ J-C ⁽¹⁾	°C/W	1000

Note:

(1) Thermal resistance from junction to ambient and from junction to case mounted on P.C.B. with 25.4mm*25.4mm copper pad areas





■Characteristics

Fig 1: Static Characteristics

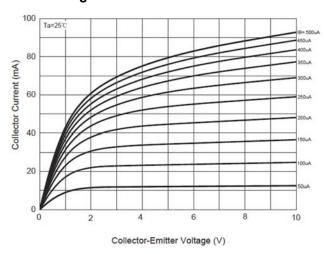


Fig 3: Collector-Emitter Saturation Voltage

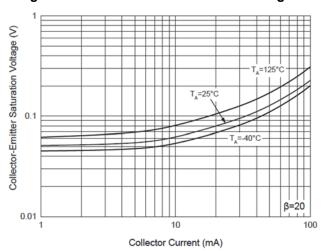


Fig 5: Base-Emitter Voltage

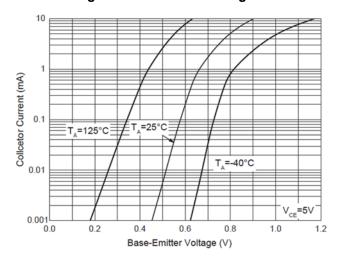


Fig 2: DC Current Gain Characteristics

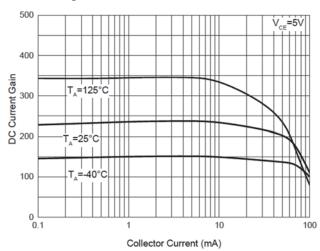


Fig 4: Base-Emitter Saturation Voltage

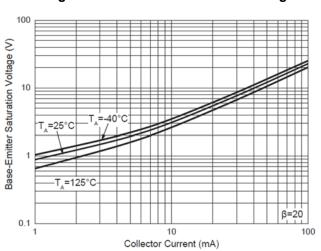
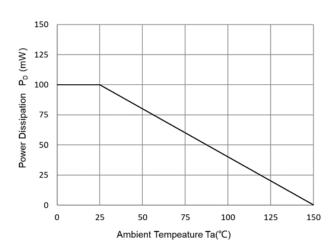


Fig 6: P_D-Ta Curve



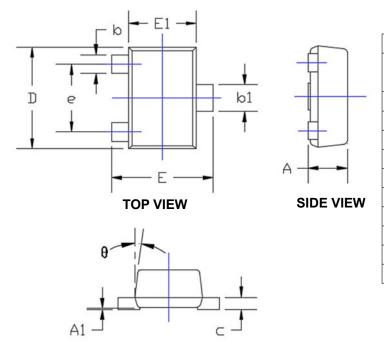




■Ordering Information

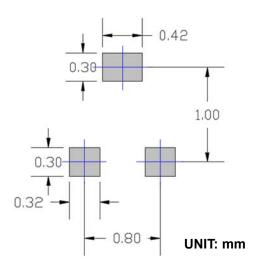
Preferred P/N	Packing code	Unit weight(g)	Minimum package(pcs)	Inner box quantity(pcs)	Outer carton quantity(pcs)	Delivery mode
DTC143TM	F2	Approximate 0.0013	8000	80000	320000	7" reel

■ Outline Dimensions



DIMENSIONS						
SYMBOL	1I	NCHES	Millimeter			
	MIN.	MAX.	MIN.	MAX.		
Α	0.017	0.022	0.430	0.550		
A1	0.000	0.002	0.000	0.050		
b	0.007	0.011	0.170	0.270		
b1	0.011	0.015	0.270	0.370		
С	0,003	0.008	0.080	0.200		
D	0.045	0.049	1.150	1,250		
Е	0.045	0.049	1.150	1,250		
E1	0.030	0.033	0.750	0.850		
6	0.03	1TYP,	0.800TYP.			
θ	7°REF.		7°REF.			

■ Suggested Pad Layout



SIDE VIEW



DTC143TM



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